

substance: boron compounds with group II elements
property: properties of beryllium-aluminum-boron compounds

There are numerous compounds of the approximate chemical compositions $\text{Al}_{\sim(1 \pm x)}\text{Be}_{\sim(1 \pm y)}\text{B}_{22}$ ($x+y \sim 2$) with $\alpha\text{-AlB}_{12}$ type structure. For details and references see AlBeB_{22} .

The compound $\text{Al}_{1.0}\text{Be}_{0.7}\text{B}_{22}$ [79H] and the compound $(\text{Be},\text{Al})\text{B}_{12}$ with the "believed" composition $\text{Be}_{0.1}\text{Al}_{0.9}\text{B}_{12}$ [79G] are subsumed here (see also [68B, 75B, 72K]).

Structure

The crystal structure is strongly related to that of $\alpha\text{-AlB}_{12}$, but the metal distribution is different. The beryllium atoms are accommodated in the two types of truncated tetrahedral holes which are vacant in $\alpha\text{-AlB}_{12}$ [79H].

position and occupancy of the metal atoms
(data from [79H])

Atom	Position	Occupancy [%]	
		$\text{Al}_{1.0}\text{Be}_{0.7}\text{B}_{22}$	$\alpha\text{-AlB}_{12}$
Al_1	8(b)	35.1(6)	71.7(7)
Al_2	8 (b)	29.1(7)	49.1(3)
Al_3	8(b)	38.7(7)	24.0(6)
Al_4	8(b)	0	15.0(3)
Al_5	8(b)	0	2.1(5)
Be_1	8(b)	46(3)	0
Be_2	4(a)	42(6)	0

space group: $\text{D}_4^4 - \text{P4}_12_12$ or $\text{D}_4^8 - \text{P4}_32_12$.

lattice parameters

a	10.180(2) Å	79H
c	14.257(2) Å	

Physical properties

energy gaps

E_g	2.12 eV	$T = 300 \text{ K}$	optical absorption	79G
	2.1 eV	$T \geq 800 \text{ K}$	electrical conductivity (see Fig. 1)	

activation energies

E_A	0.7 eV	$T = 300 \dots 500 \text{ K}$	electrical conductivity (see Fig. 1)	79G
	0.55 eV	$T = 200 \dots 300 \text{ K}$		

trap density

n_t	$4 \cdot 10^{13} \text{ cm}^{-3}$	$I - U^2$ region	$I - U$ characteristic	79G
-------	-----------------------------------	------------------	------------------------	-----

electrical conductivity: Fig. 1

$I-U$ characteristic: Fig. 2

lattice absorption spectrum: Fig. 3

dielectric constants

$\varepsilon(0)$	18	$T = 300\text{ K}$	improbable value (cp. comment to Fig. 3)	79G
$\varepsilon(\infty)$	8.3	$T = 300\text{ K}$	interferences, platelets $d = 50\ldots 100\text{ }\mu\text{m}$; $\lambda = 2\ldots 9\text{ }\mu\text{m}$	79G

References:

- 68B Becher, H. J., Neidhard, H.: Acta Crystallogr. B 24 (1968) 280.
- 72K Krogmann, K., Becher, J. H.: Z. Anorg. Allg. Chem. 392 (1972) 197.
- 75B Becker, H. J., Rethfeld, H., Mattes, R.: Z. Anorg. Allg. Chem. 414 (1975) 203.
- 79G Golikova, O. A., Kazanin, M. M., Orlov, V. M., Tkalenko, E. N., Fedorov, M. I.: J. Less-Common Met. 67 (1979) 363.
- 79H Higashi, I.: J. Less-Common Met. 67 (1979) 7.

Fig. 1.

$\text{Be}_{0.1}\text{Al}_{0.9}\text{B}_{12}$. Conductivity vs. reciprocal temperature [79G].

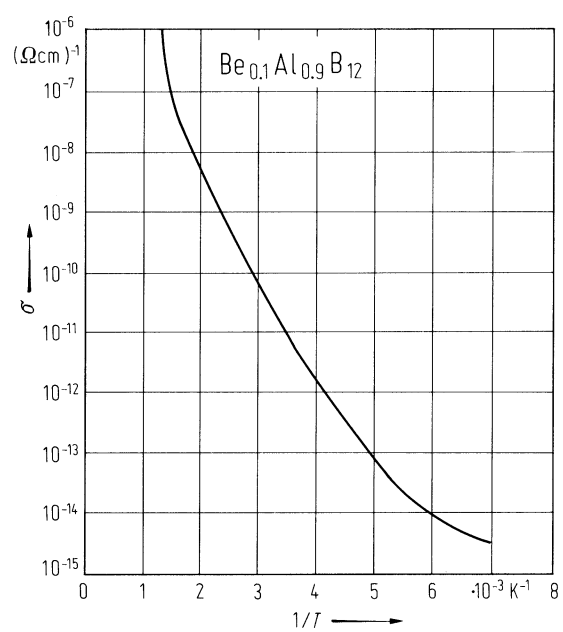


Fig. 2.

$\text{Be}_{0.1}\text{Al}_{0.9}\text{B}_{12}$. Current-voltage characteristics at various temperatures. Curve 1: $T = 113$ K; curve 2: $T = 145$ K; curve 3: $T = 185$ K; curve 4: $T = 232$ K; curve 5: $T = 293$ K [79G].

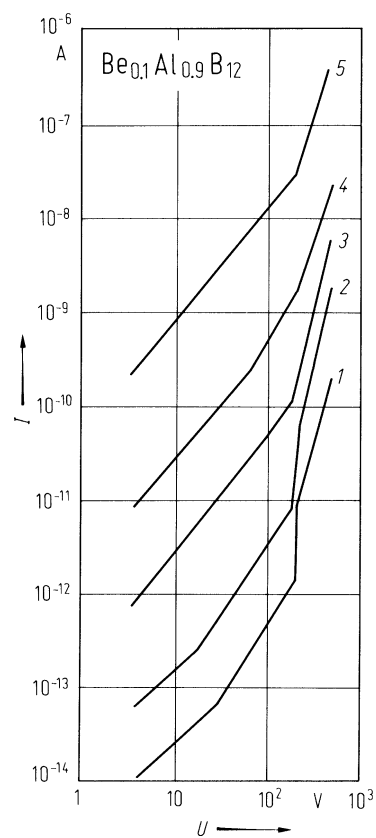


Fig. 3.

$\text{Be}_{0.1}\text{Al}_{0.9}\text{B}_{12}$. Absorption coefficient K and reflectivity R vs. wavelength. (Remark: the strong increase of the reflectivity with increasing wavelength cannot be explained by lattice vibrations of such low oscillator strengths. Hence $\epsilon(0)$, which has been derived from R should be put in question, too.) [79G].

